

Fig.1

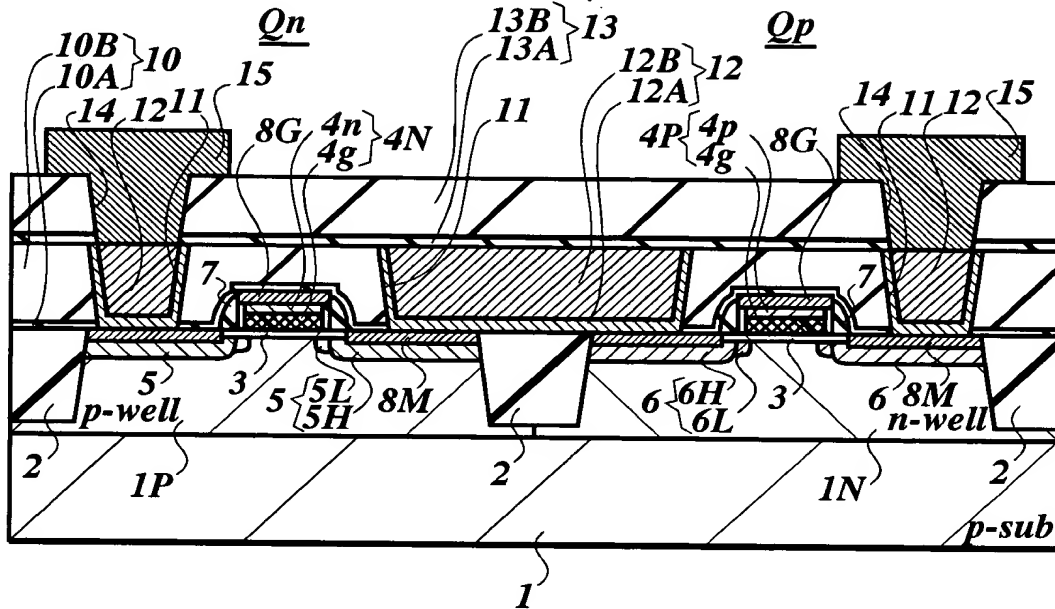


Fig.2

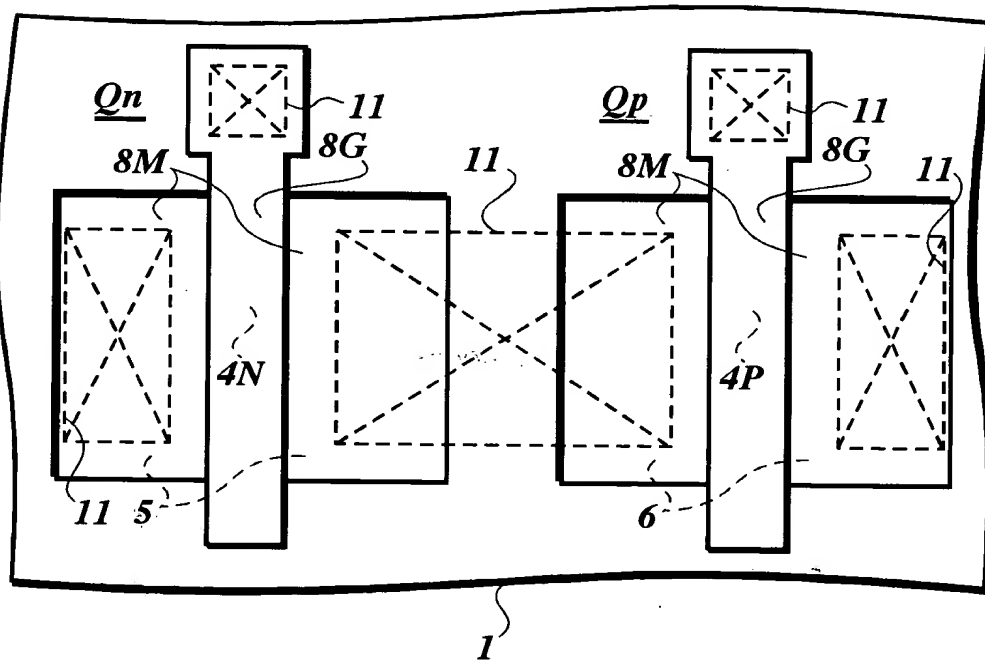


Fig.3

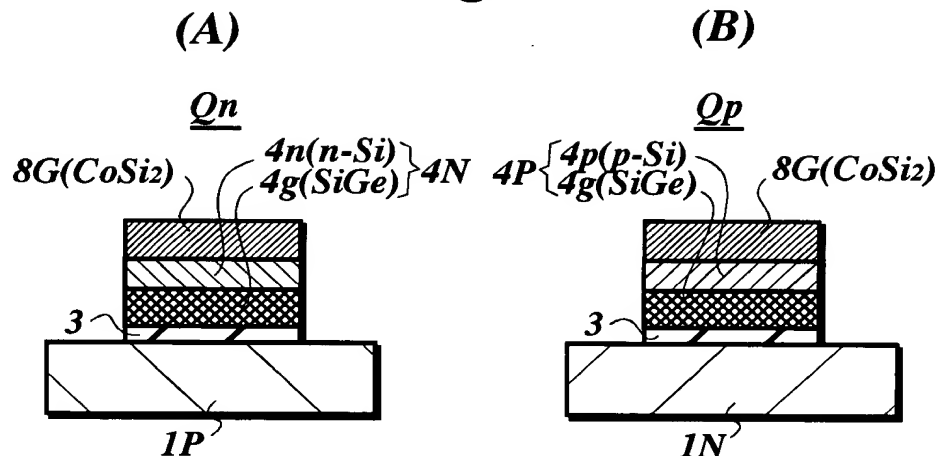


Fig.4

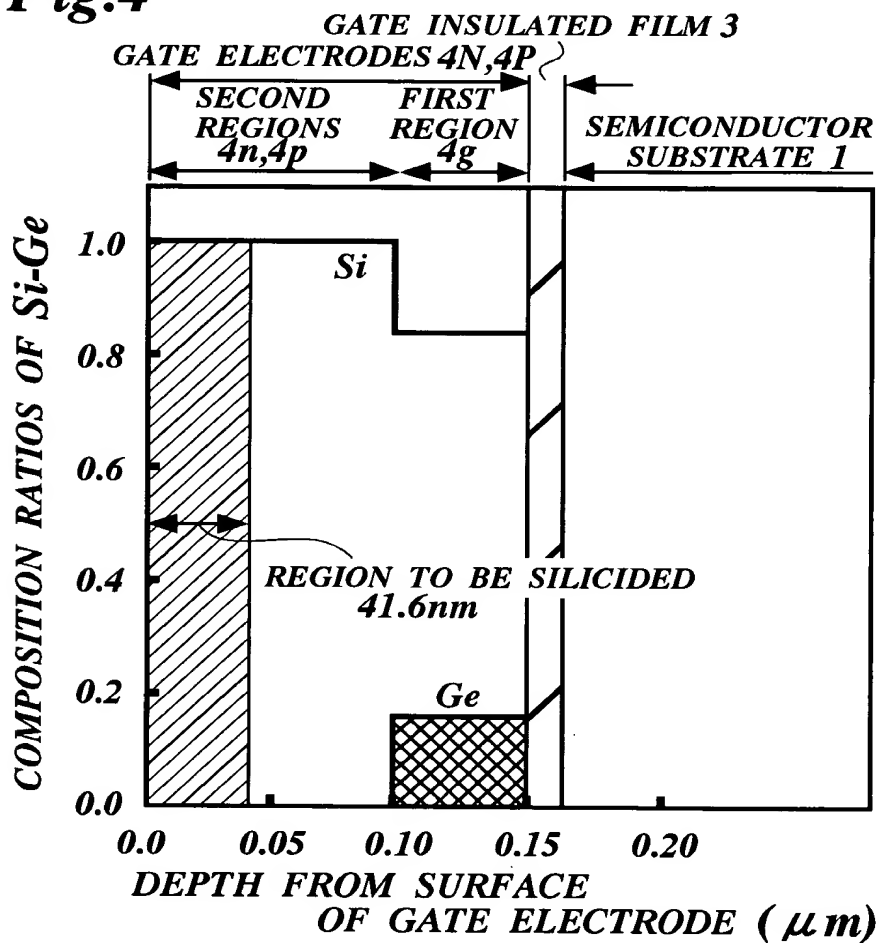


Fig.5

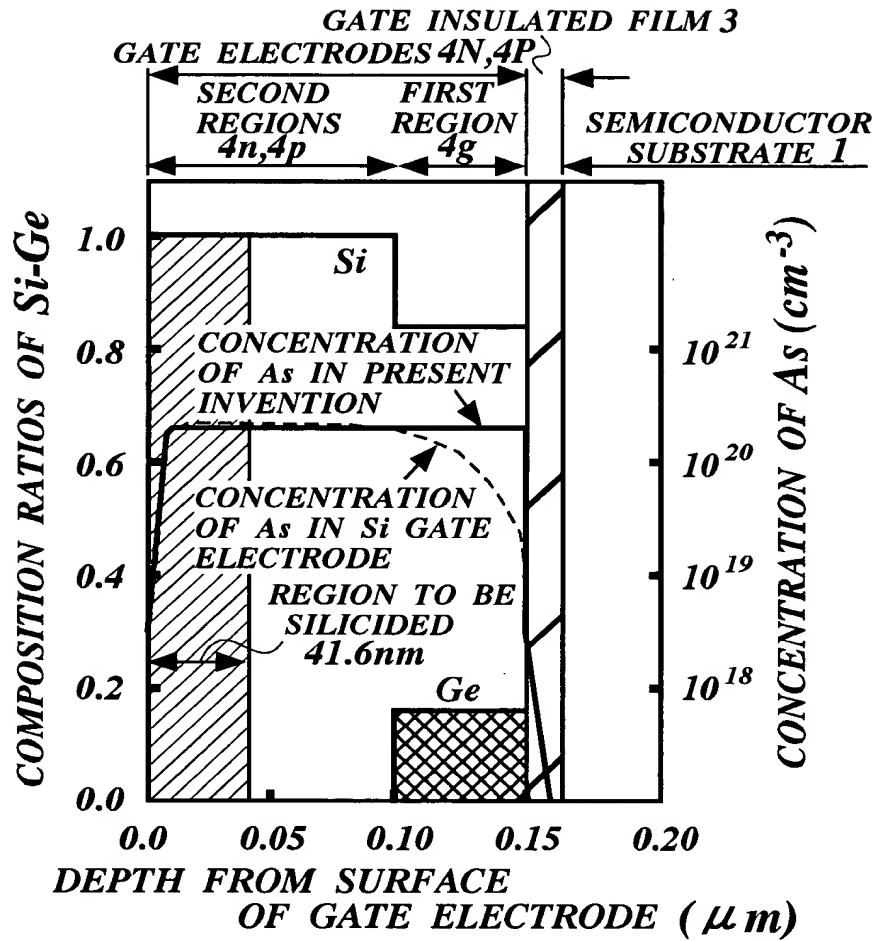


Fig.6

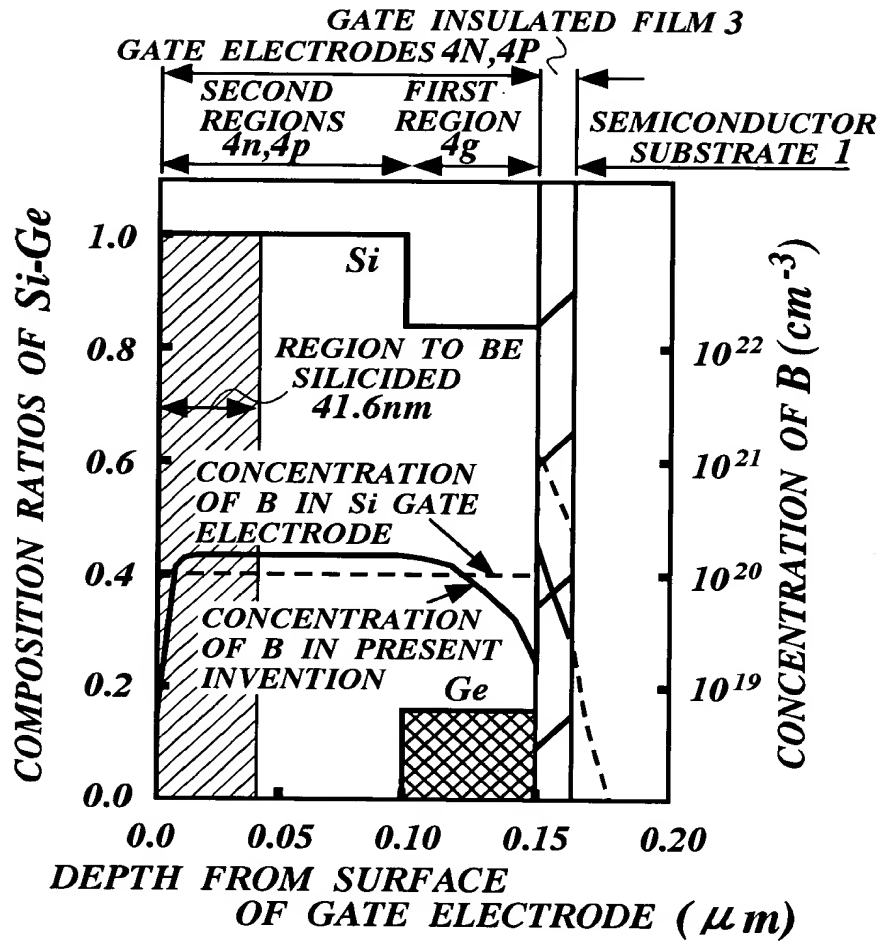


Fig.7

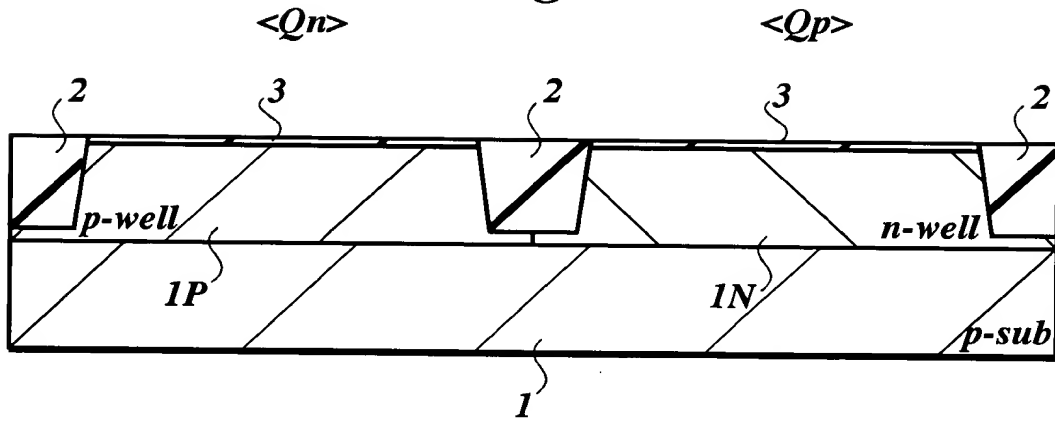


Fig.8

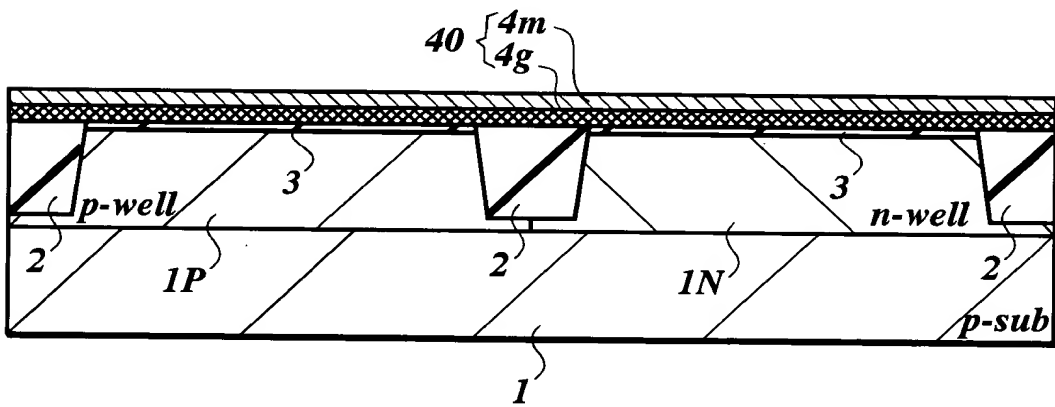


Fig.9

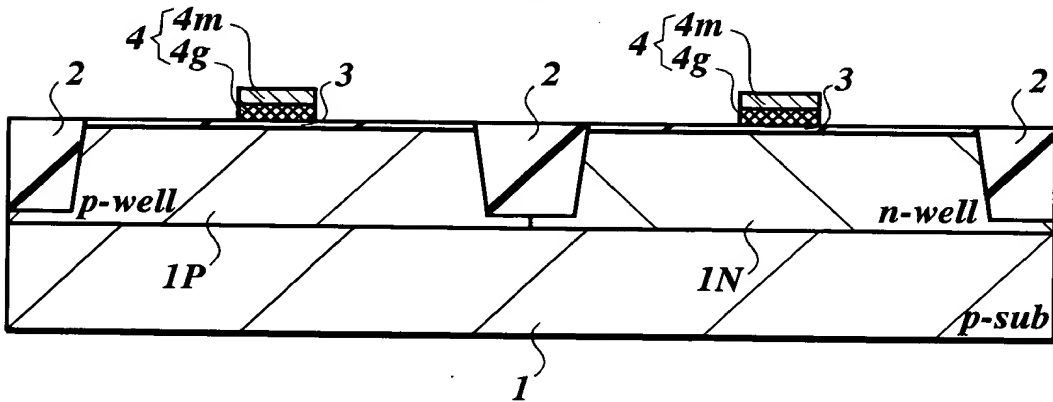


Fig.10

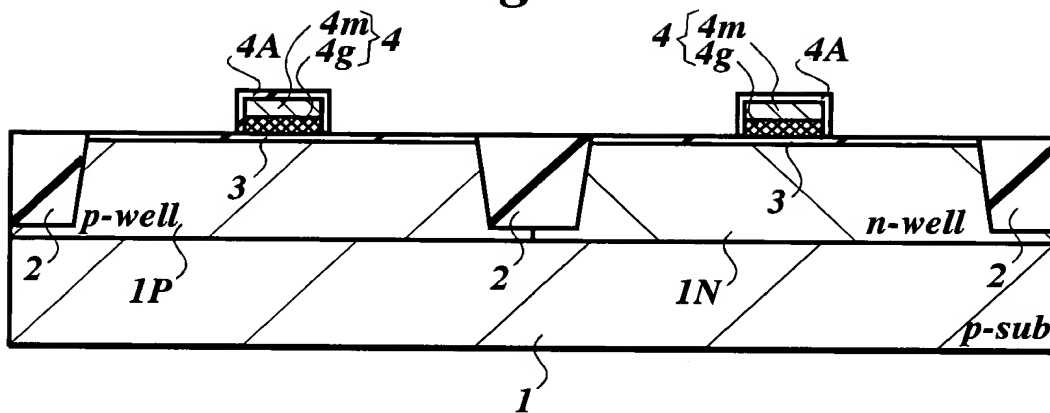


Fig.11

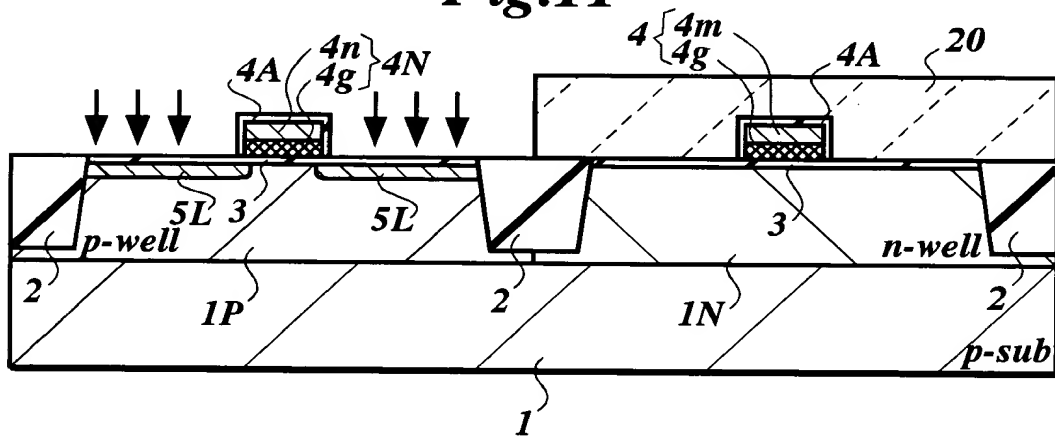
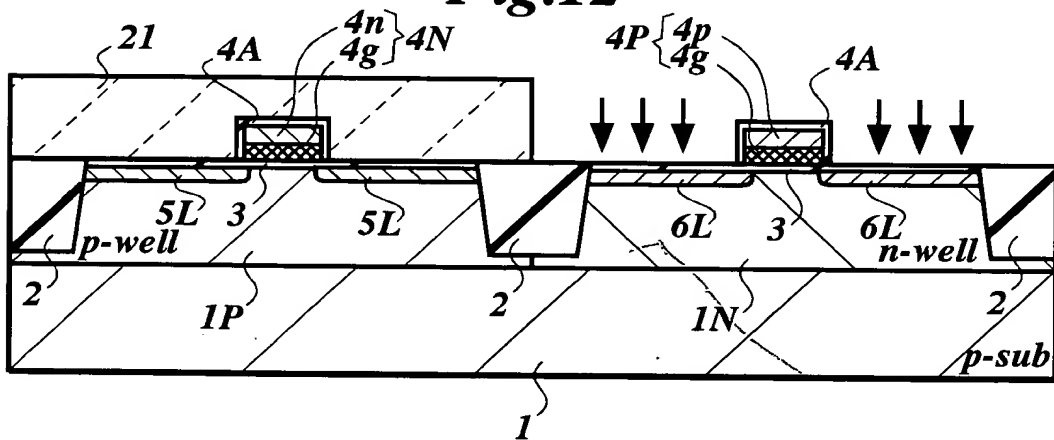
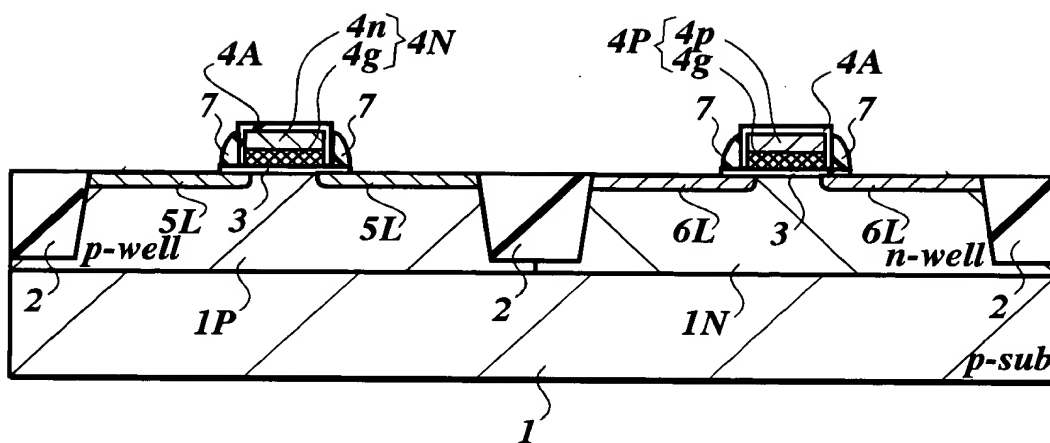


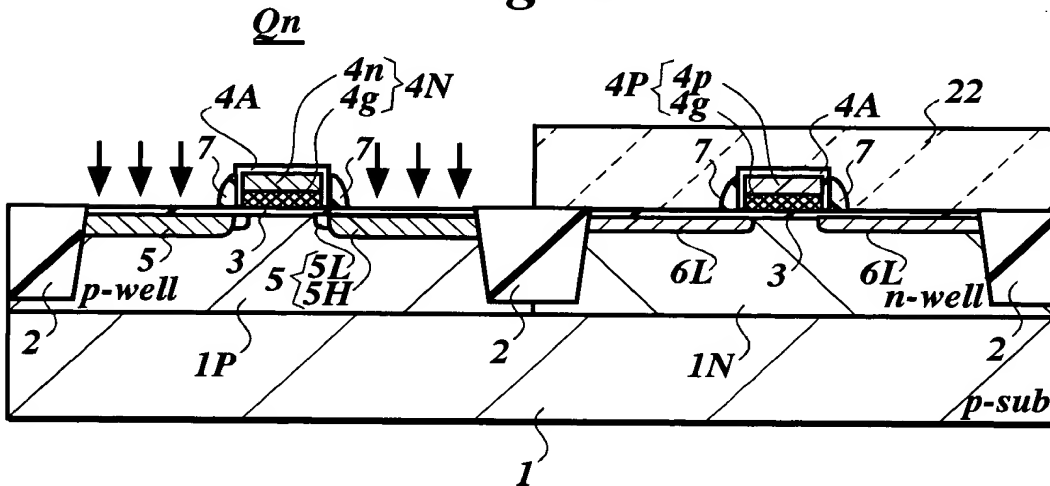
Fig.12



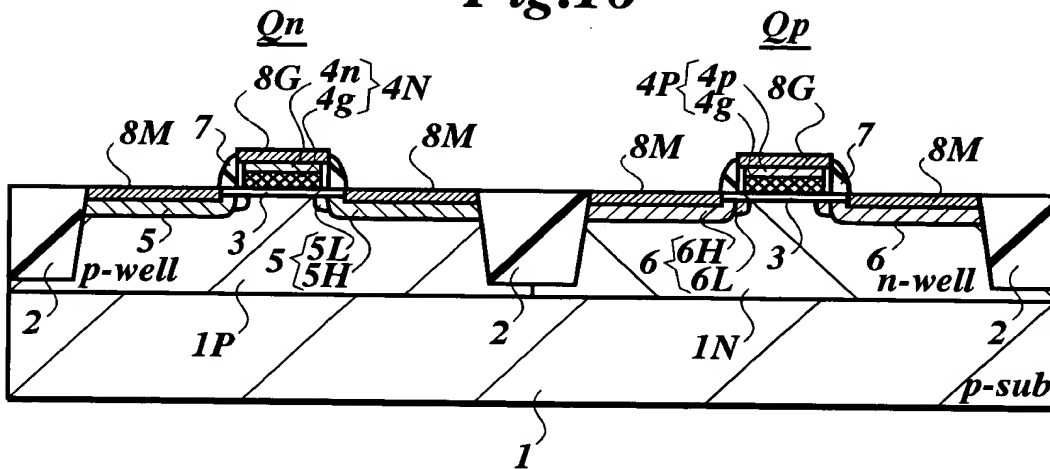
***Fig.13***



***Fig.14***

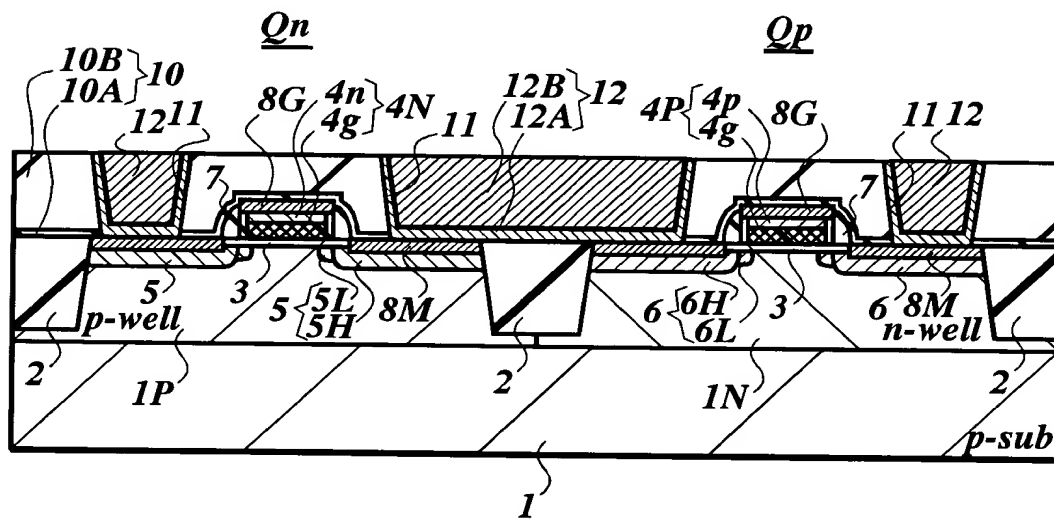


***Fig.16***

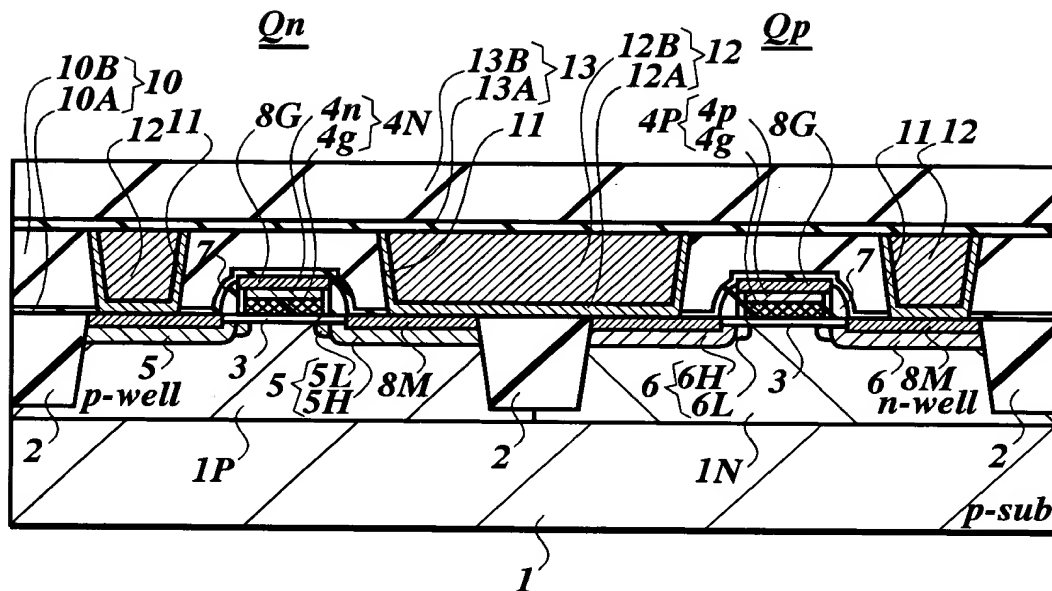




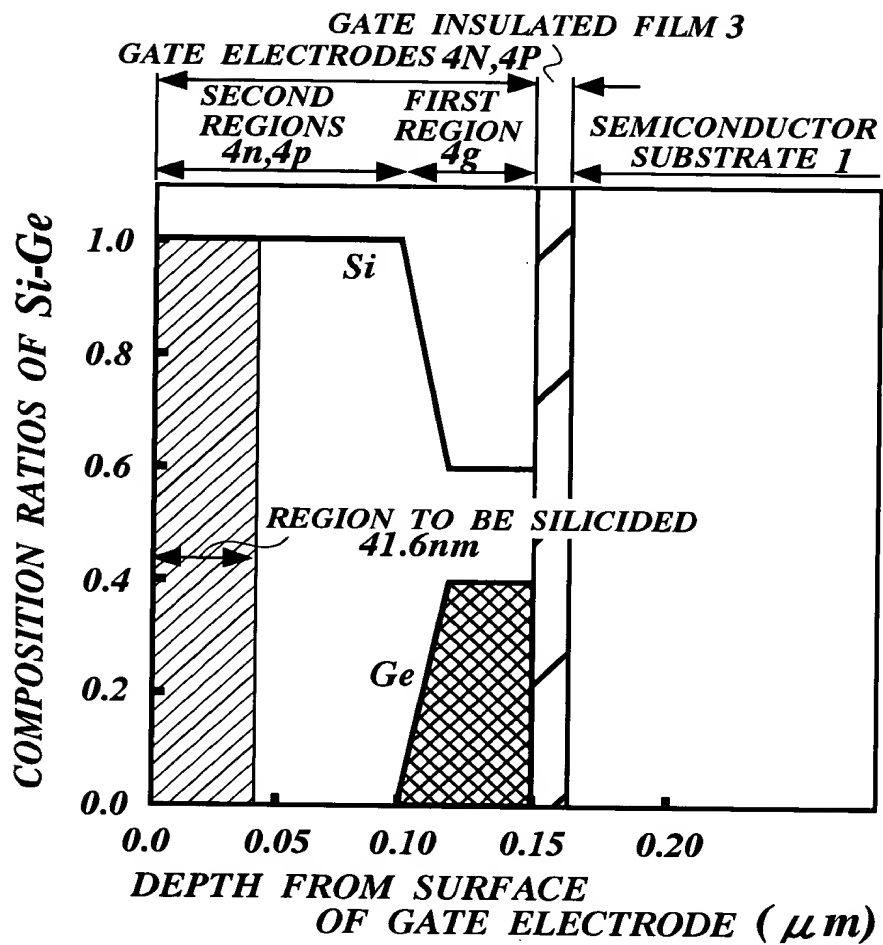
***Fig.18***



***1***

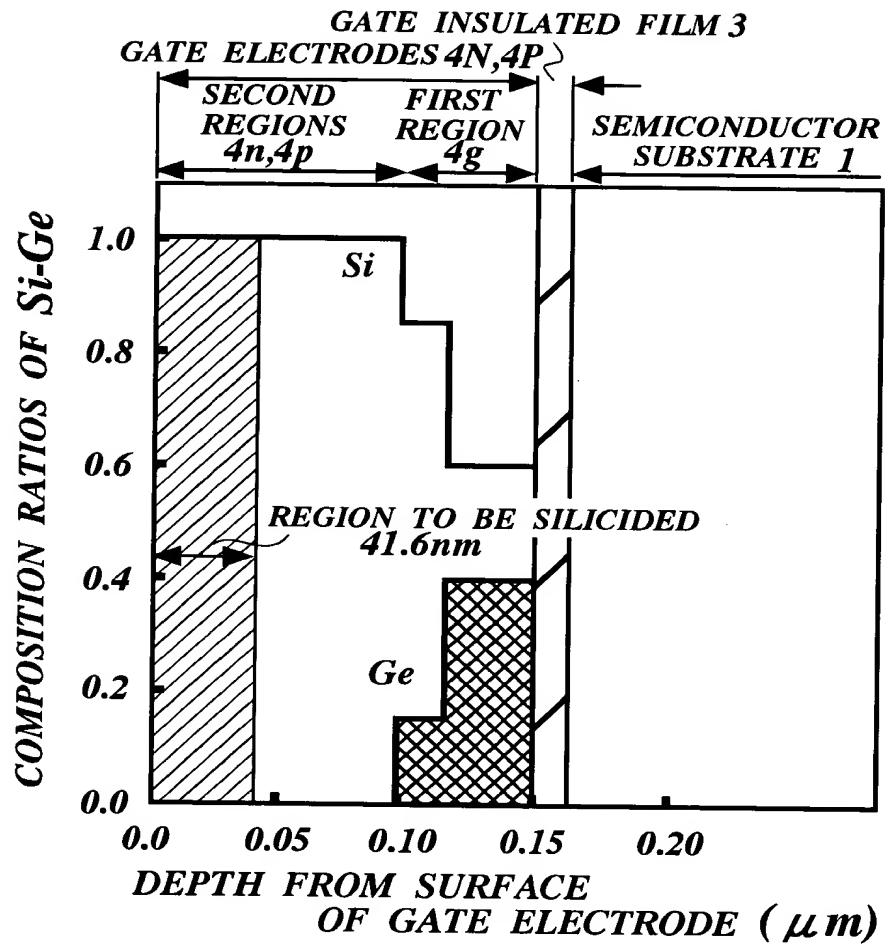


***Fig.20***



12/23

Fig.21



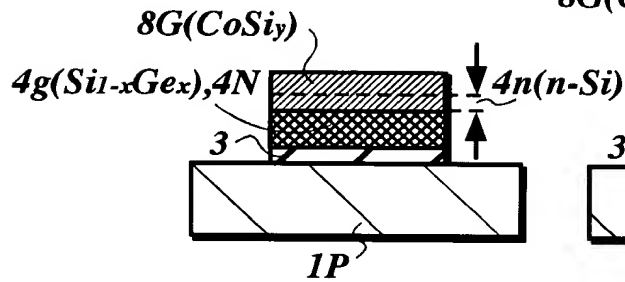
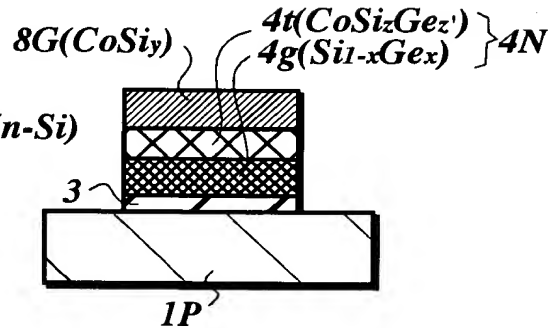
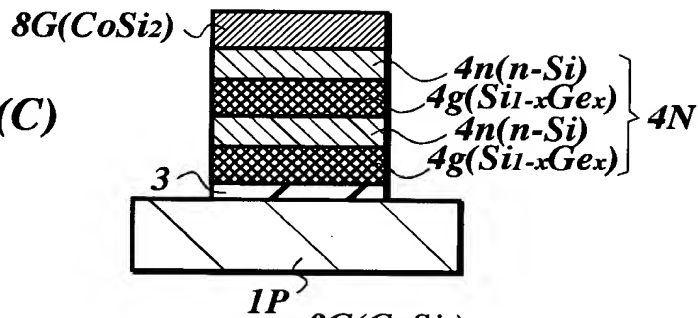
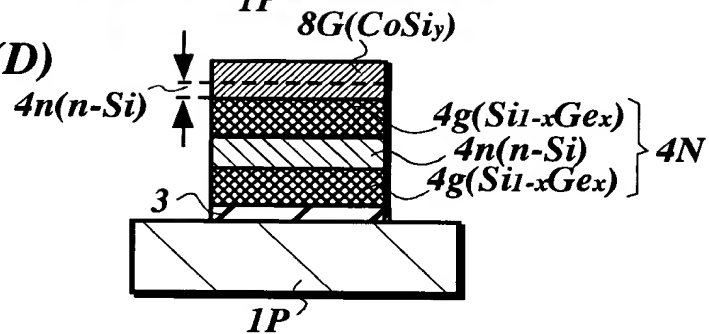
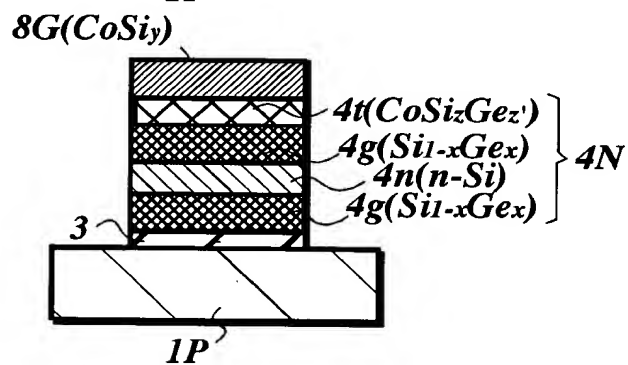
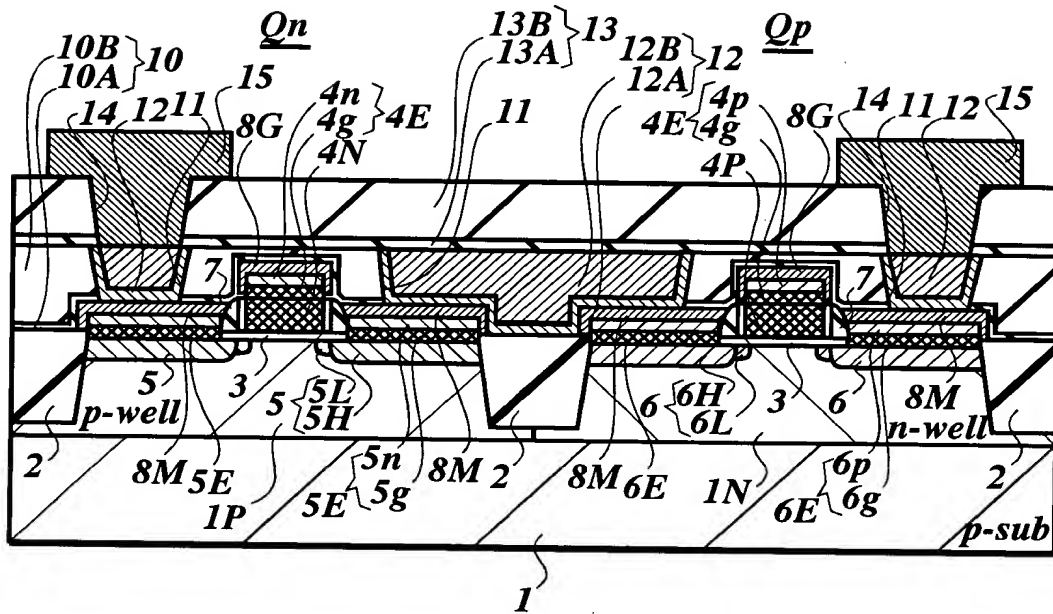
**Fig.22 (A)****Fig.22 (B)****Fig.22 (C)****Fig.22 (D)****Fig.22 (E)**

Fig.23



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Fig.24

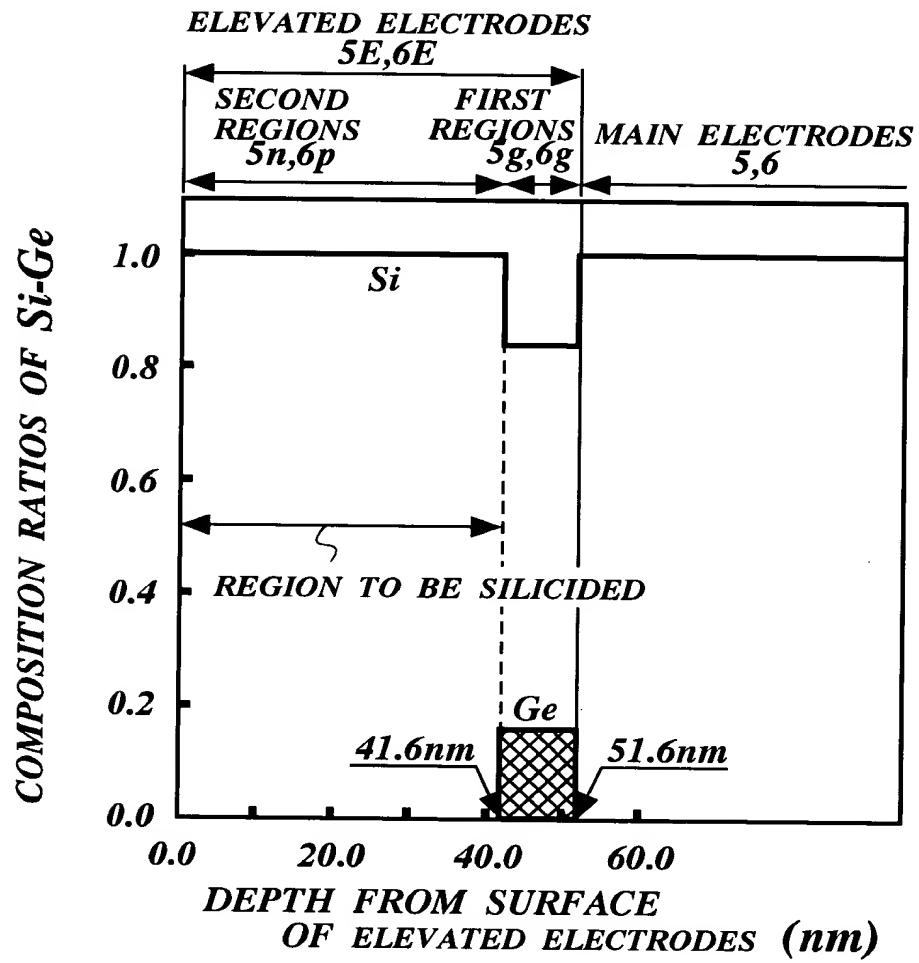


Fig.25

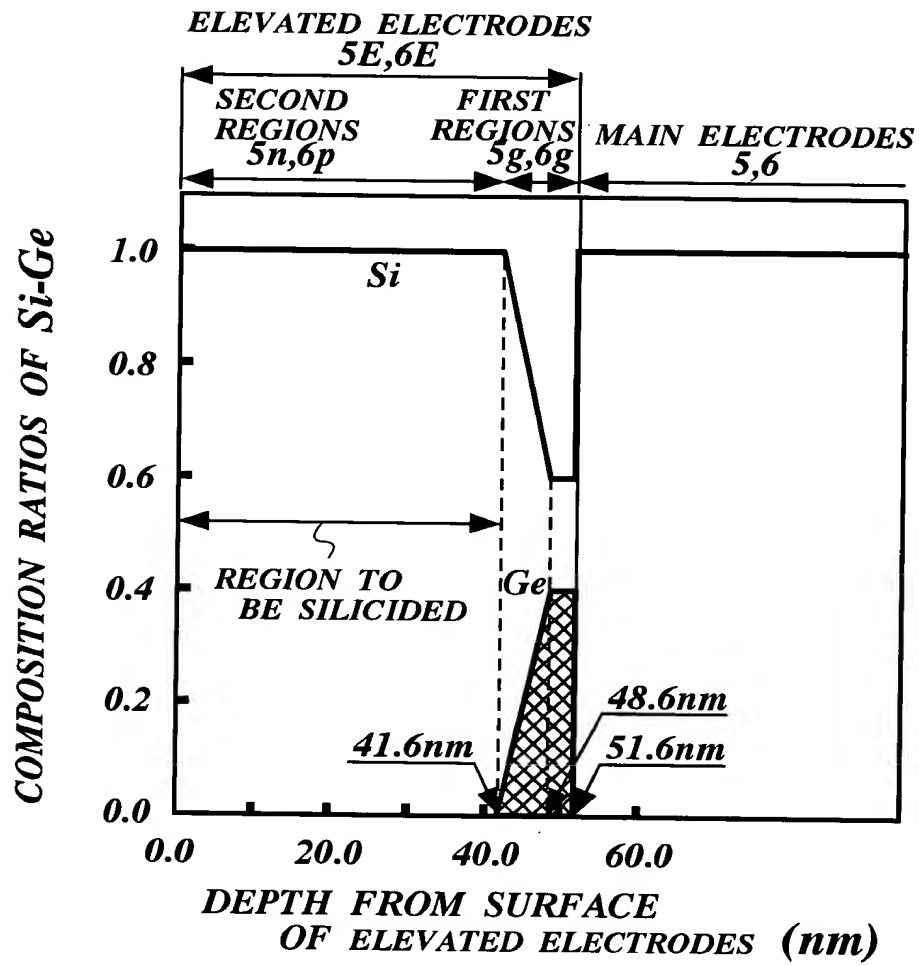




Fig.26

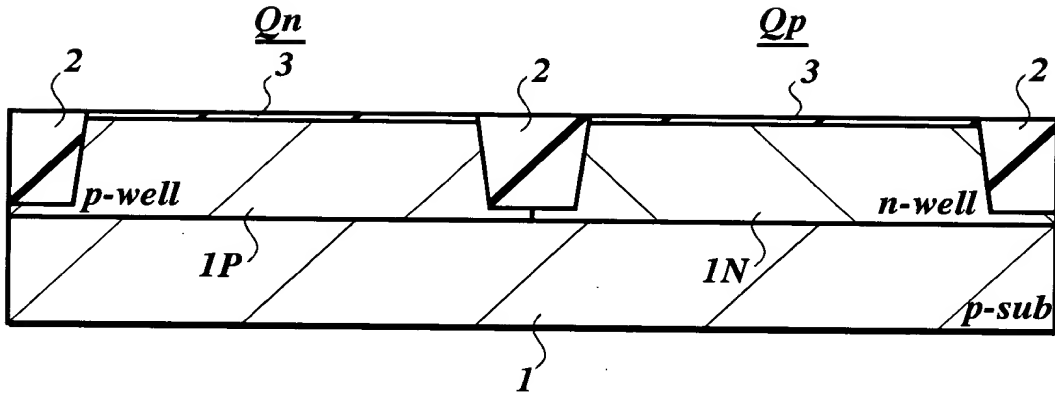


Fig.27

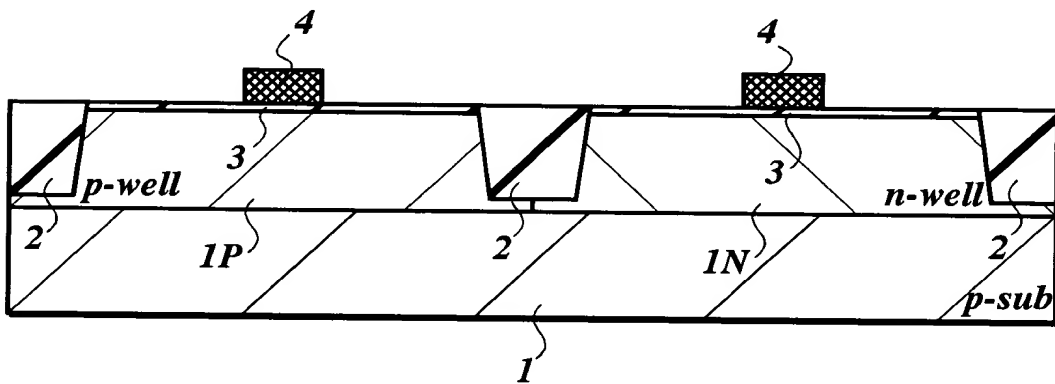


Fig.28

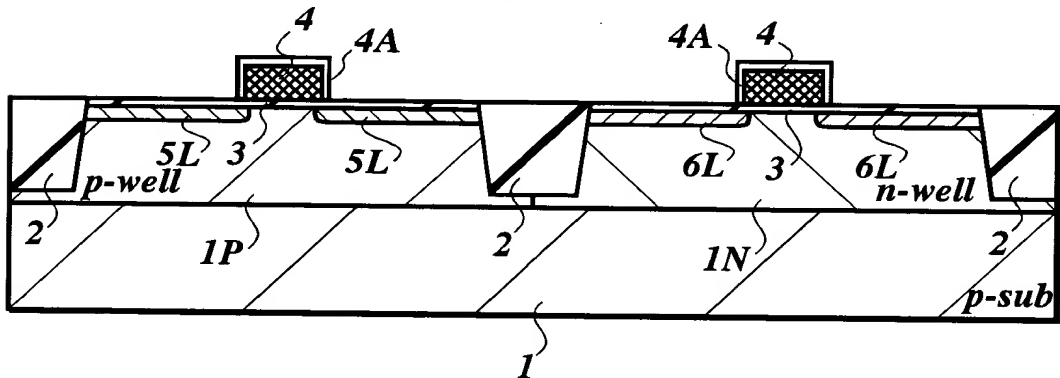


Fig.29

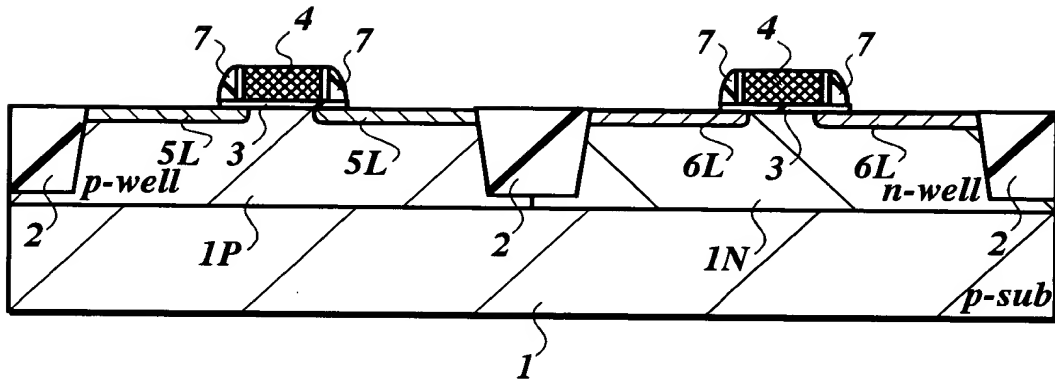
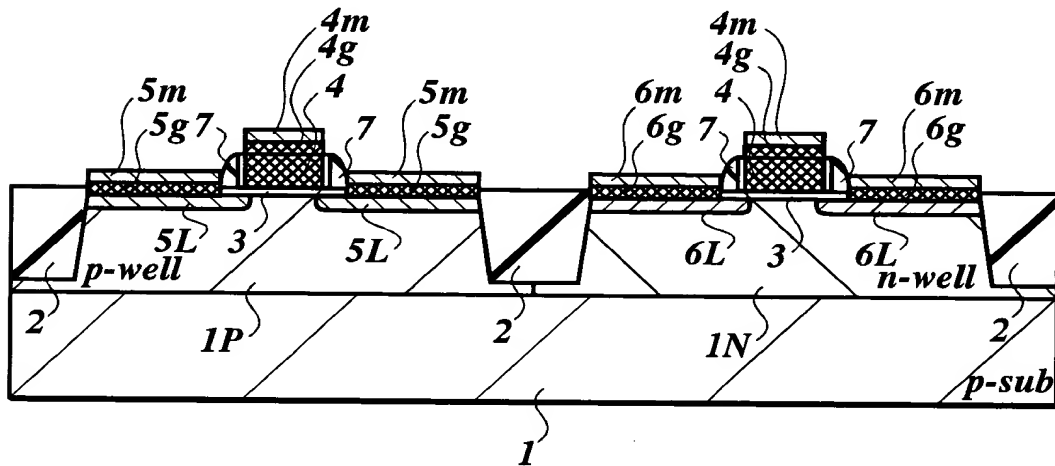


Fig.30



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Fig.31

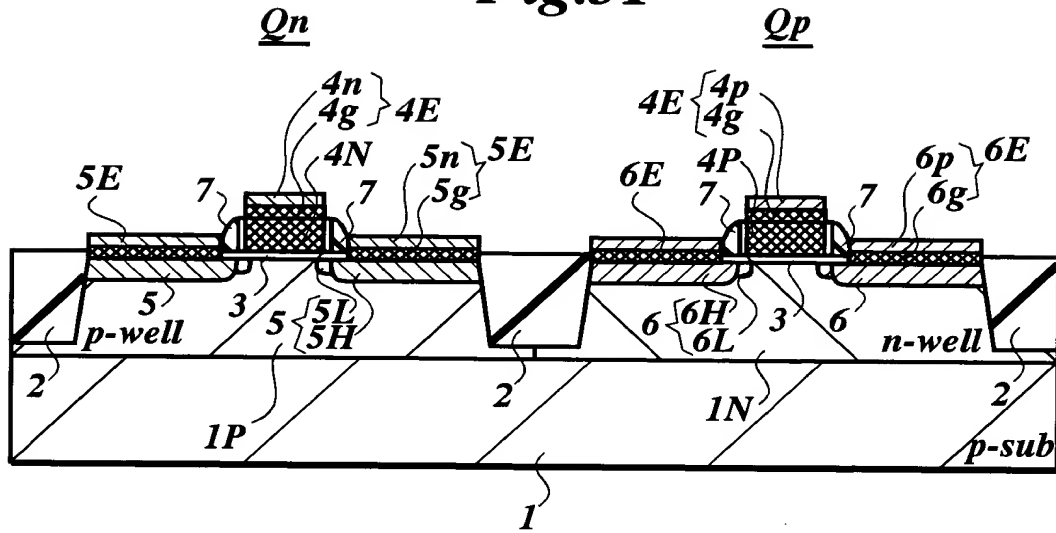
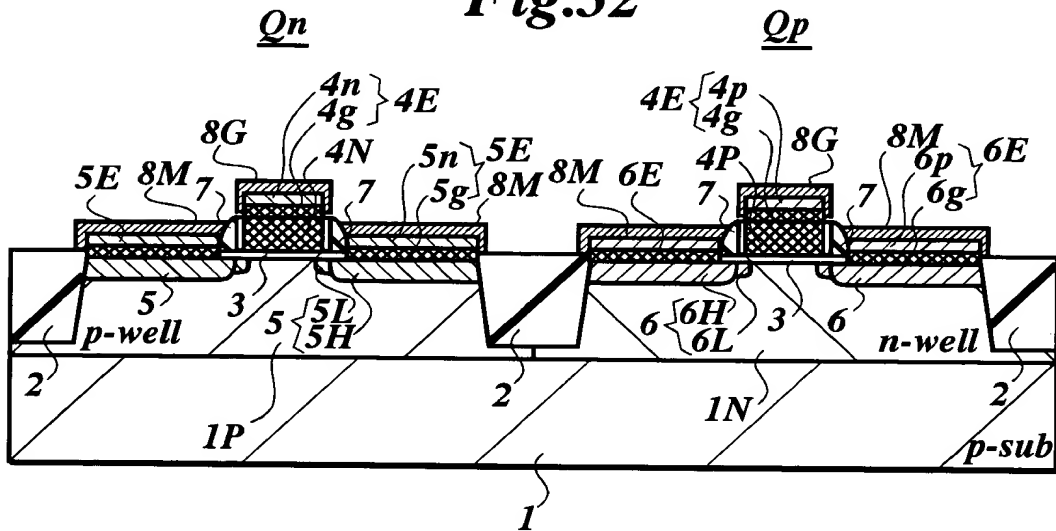


Fig.32





The diagram shows a cross-sectional view of a semiconductor device. It consists of several layers and regions. At the bottom is a layer labeled  $p\text{-sub}$ . Above this is a layer divided into two main sections:  $1P$  on the left and  $1N$  on the right. In the  $1P$  section, there is a  $p\text{-well}$ . In the  $1N$  section, there is an  $n\text{-well}$ . Above these wells is a layer labeled  $2$ , which has a central protrusion or gate-like structure. The topmost layer is labeled  $3$ . Labels  $\underline{Qn}$  and  $\underline{Qp}$  are positioned above the  $1P$  and  $1N$  regions respectively. A label  $l$  is at the very bottom center.

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Fig.37

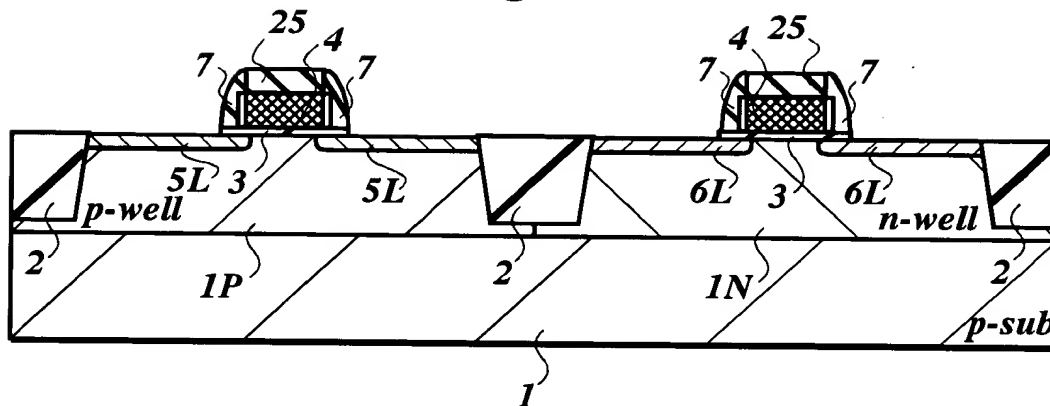


Fig.38

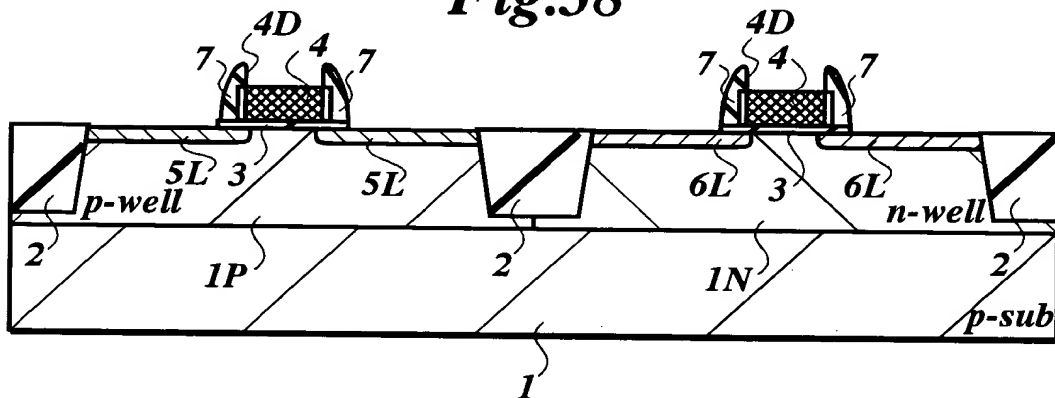


Fig.39

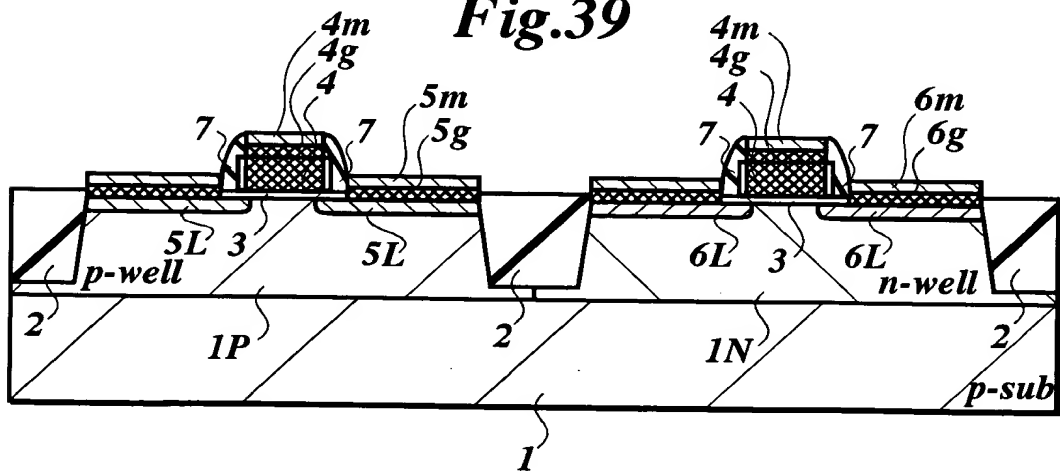


Fig.40

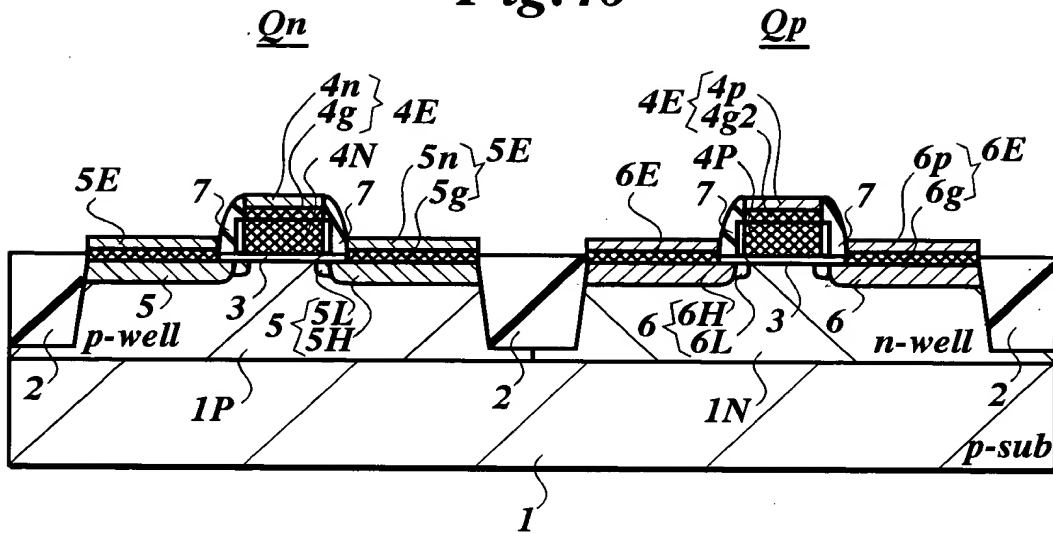


Fig.41

